

SEMICONDUCTOR DEVICE

BACKGROUND OF THE INVENTION

The present invention relates to a method for separately measuring capacitive components in a semiconductor device and a Test Element Group (TEG) pattern having its function.

In the design and development of high-performance LSIs, it is significant to sample (measure) the characteristics of semiconductor elements placed in an LSI with high accuracy, and a technique for sampling (measuring) the same and the optimal design of a TEG are required.

In recent years, as semiconductor elements become finer, the influences of noises caused by crosstalk and the degradation of delay characteristics due to a Miller capacitance have become more obvious. Therefore, it has been required to sample capacitive components of individual conductor members, such as interconnects and semiconductor layers, of the characteristics of the semiconductor device with high accuracy.

A technique for sampling parasitic capacitances as disclosed in Patent Document 1 (US Patent 6,300,765 B1) has been conventionally known. The objective of this technique is to separately measure interconnect-to-interconnect capacitances C12 and C13.

Figure 7 is a circuit diagram illustrating the structure of a capacitance measuring circuit for measuring parasitic capacitances as disclosed in Patent Document 1.

As shown in this figure, a P-type Metal Insulator Semiconductor Field Effect Transistor (PMISFET) 101 and an N-type Metal Insulator Semiconductor Field Effect Transistor) 102 are connected in series to each other, and the drain of each of the PMISFET 101 and the NMISFET 102 is connected via a node N1 to an interconnect W1. The source of the PMISFET 101 is connected to a power supply pad PST for supplying a power supply voltage Vdd, while the source of the NMISFET 102 is connected to a ground pad GND (voltage Vss). The gate of the PMISFET 101 is connected to a charging pad

111, while the gate of the NMISFET 102 is connected to a discharging pad 112. Furthermore, there are provided an interconnect W2 arranged in a layer higher than the interconnect W1 and crossing the interconnect W1 when viewed in a plane, and an interconnect W3 extending substantially parallel to the interconnect W1 and crossing the interconnect W2 when viewed in the same plane. The interconnect W2 is connected to a first pad 113 for measuring current via a node N2 and an NMISFET 103, while the interconnect W3 is connected to a second pad 114 for measuring current via a node N3 and an NMISFET 104. The gate of each of the NMISFETs 103 and 104 is connected to a current-monitoring pad 115. The capacitance measuring circuit is configured so that it can measure currents I1 and I2 by bringing the first and second pads 113 and 114 for measuring current into contact with probes of ammeters 121 and 122, respectively. When the probes of the ammeters 121 and 122 come into contact with the pads 113 and 114 for measuring current, respectively, the sources of the NMISFETs 103 and 104 are fixed at 0V.

The interconnect W2 is connected via an NMISFET 105 to the ground pad GND, while the interconnect W3 is connected via an NMISFET 106 to the ground pad GND.

Here, the capacitance between the interconnects W1 and W2 is designated C12, the capacitance between the interconnects W1 and W3 is designated C13, and the capacitance between the interconnects W2 and W3 is designated C23. In this relation, the capacitance C12 is a value obtained by dividing a charge induced in the interconnect W2 when a voltage is applied to the interconnect W1, by the applied voltage. The capacitance C13 is a value obtained by dividing a charge induced in the interconnect W3 when a voltage is applied to the interconnect W1, by the applied voltage.

Figure 8 is a timing diagram illustrating the operation of the capacitance measuring circuit shown in Figure 7. The known capacitance measuring circuit operation will be described with reference to Figure 8.

First, the power supply voltage Vdd is fixed at a voltage Vcc, while the ground

voltage V_{ss} is fixed at 0V. A charging voltage V_{111} and a discharging voltage V_{112} are switched between the voltages V_{cc} and V_{ss} such that both of the PMISFET 101 and the NMISFET 102 are not ON at any timing. However, there exists a timing at which both of the PMISFET 101 and the NMISFET 102 are OFF. Therefore, no flow-through current
 5 passing through both of the PMISFET 101 and the NMISFET 102 is produced.

Between timings t_0 and t_1 , the discharging voltage V_{112} is held at the voltage V_{cc} so that the NMISFETs 102, 105 and 106 are ON. Therefore, the potentials of the nodes N1, N2 and N3 are fixed at the ground voltage V_{ss} .

Between timings t_1 and t_2 , all the MISFETs 101, 102, 103, 104, 105, and 106 are
 10 OFF.

Between timings t_2 and t_3 , since the PMISFET 101 and the NMISFET 102 are OFF, and the NMISFETs 103 and 104 are ON, it is possible to monitor currents.

Between timings t_3 and t_4 , since the PMISFET 101 is ON, a charge from the interconnect W1 to the interconnects W2 and W3 is induced. At this time, currents are
 15 monitored using the ammeters 121 and 122, thereby measuring the capacitances C12, C13 and C23. The time between the timings t_3 and t_4 is set at a time enough to induce a charge in the interconnect W1 and monitor the currents using the ammeters 121 and 122.

Between timings t_4 and t_5 , the PMISFET 101 is OFF.

Between timings t_5 and t_6 , since all the MISFETs are OFF, it becomes impossible to
 20 monitor the currents.

Between timings t_6 and t_7 , the same operations as between the timings t_0 and t_1 are carried out. Thereafter, the above-mentioned operations for the timings t_1 through t_7 are periodically repeated.

The value to be observed by a measuring device using this circuit is a mean value
 25 between the currents I1 and I2 detected over time by the ammeters 121 and 122, respectively. When the frequency of the gate input waveform is $f(=1/T)$ (T denotes the time from the timing t_0 to the timing t_7), the following formulae (1) and (2) hold:

$$I1=C12 \cdot V_{cc} \cdot f \quad (1)$$

$$I2=C13 \cdot V_{cc} \cdot f \quad (2)$$

By using the formulae (1) and (2), measured capacitance values **C12** and **C13** are obtained from the following formulae (3) and (4):

$$C12=I1/(V_{cc} \cdot f) \quad (3)$$

$$C13=I2/(V_{cc} \cdot f) \quad (4)$$

This known technique is characterized in that the desired capacitances **C12** and **C13** can directly be measured without the need for canceling the parasitic capacitance of a transistor.

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SUMMARY OF THE INVENTION

The known technique, however, has the following defects:

(1) the capacitance value **C23** between the interconnects **W2** and **W3** as shown in Figure 7 cannot be measured using a circuit pattern shown in Figure 7;

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(2) even when the circuit pattern shown in Figure 7 is used, the charge induced in the interconnect **W1** when a voltage is applied to the interconnect **W2** and the charge induced in the interconnect **W1** when a voltage is applied to the interconnect **W3** cannot be measured; and

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(3) the number of pads is large for the number of measurable items and typically the area of each of the pads is approximately $100\mu\text{m} \times 100\mu\text{m}$, leading to an increase in the area occupied by the semiconductor device.

Furthermore, concerning the defect (2), the difference between $C_{gd}(=dQ_g/dV_d)$, Q_g : gate charge, V_d : drain voltage) and $C_{dg}(=dQ_d/dV_g)$, Q_d : drain charge, V_g : gate voltage) in the MIS capacitance cannot be measured.

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It is an object of the present invention to provide a semiconductor device including a capacitance measuring circuit that can separately measure capacitance components.

The semiconductor device of the present invention comprises a capacitance

measuring circuit in which, when there exist first through third conductor members, the first and second conductor members are connected via respective switching transistors to a common charging voltage supply part and the second and third conductor members are connected via respective switching transistors to a current sampling part.

5 Thereby, besides parasitic capacitances between the first and second conductor members and parasitic capacitances between the first and third conductor members, parasitic capacitances between the second and third conductor members can also be measured. Only two pads connected to a charging voltage supply part and a current sampling part, respectively become necessary on a semiconductor chip corresponding to
10 the capacitance measuring circuit. Therefore, the number of pads of the whole semiconductor device can be decreased.

 Furthermore, if all the conductor members are chargeable and dischargeable, then the parasitic capacitance caused between the second conductor member and the first conductor member when the second conductor member is charged or the parasitic
15 capacitance caused between the third conductor member and the first conductor member when the third conductor member is charged, for example, can also be measured.

 Preferably, there is provided a discharge part, and the conductor member whose parasitic capacitance is not to be measured is discharged while the parasitic capacitance between the other two conductor members is measured.

20 The first through third conductor members may be all interconnects or may be any three-way combination of a source/drain region, a substrate region and a gate electrode of a MISFET. In the latter case, the semiconductor chip has a triple well structure, thereby reducing the influence of noises in the capacitance measurement.

 If the charging voltage supply part is operated at a power supply voltage lower than
25 that supplied to a control circuit, then the influence of substrate noises leading to problems in the measurement of the capacitances representing analog quantities can be suppressed.

 There may be provided an oscillator for generating a clock signal having a higher

frequency than an external clock signal. This allows the control circuit to generate a waveform. The provision of a frequency divider facilitates external monitoring of the frequency.

5 BRIEF DESCRIPTION OF DRAWINGS

Figure 1 is a circuit diagram illustrating the structure of a capacitance measuring circuit placed in a semiconductor device according to a first embodiment.

Figure 2 is a timing diagram illustrating the time variation of gate biases that are output from a control circuit in the capacitance measurement using the capacitance
10 measuring circuit and are applied to gates of MISFETs, respectively.

Figure 3 is a circuit diagram illustrating the structure of a capacitance measuring circuit placed in a semiconductor device according to a second embodiment.

Figure 4 is a cross sectional view of the semiconductor device according to the second embodiment.

15 Figure 5 is a circuit diagram illustrating the structure of a capacitance measuring circuit placed in a semiconductor device according to a third embodiment.

Figure 6 is a circuit diagram illustrating the structure of a capacitance measuring circuit placed in a semiconductor device according to a fourth embodiment.

Figure 7 is a circuit diagram illustrating the structure of a capacitance measuring
20 circuit for measuring parasitic capacitance disclosed in Patent Document 1.

Figure 8 is a timing diagram illustrating the operation of the known capacitance measuring circuit.

DETAILED DESCRIPTION OF THE INVENTION

25 (Embodiment 1)

Figure 1 is a circuit diagram illustrating the structure of a capacitance measuring circuit placed in a semiconductor device (LSI) according to a first embodiment. The

capacitance measuring circuit located in the semiconductor device of this embodiment is configured to measure the capacitance (parasitic capacitance) between each two of three conductor members forming a target capacitor section (section to be measured in capacitance).

5 As shown in Figure 1, the target capacitor section in the semiconductor device of this embodiment is provided with three conductor members each two opposed with dielectrics interposed therebetween. The three conductor members are an interconnect **W1** (first conductor member), an interconnect **W2** (second or third conductor member) placed in a layer higher than the interconnect **W1** and crossing the interconnect **W1** when
10 viewed in a plane, and an interconnect **W3** (third or second conductor member) extending substantially parallel to the interconnect **W1** and crossing the interconnect **W2** when viewed in the same plane. Capacitances between the interconnects **W1** and **W2** are designated **C12** and **C21**, capacitances between the interconnects **W1** and **W3** are designated **C13** and **C31**, and capacitances between the interconnects **W2** and **W3** are
15 designated **C23** and **C32**. In this relation, the capacitance **C12** is a value obtained by dividing a charge induced in the interconnect **W2** when a voltage is applied to the interconnect **W1**, by the applied voltage. The capacitance **C21** is a value obtained by dividing a charge induced in the interconnect **W1** when a voltage is applied to the interconnect **W2**, by the applied voltage. The capacitance **C13** is a value obtained by
20 dividing a charge induced in the interconnect **W3** when a voltage is applied to the interconnect **W1**, by the applied voltage. The capacitance **C31** is a value obtained by dividing a charge induced in the interconnect **W1** when a voltage is applied to the interconnect **W3**, by the applied voltage. The capacitance **C23** is a value obtained by dividing a charge induced in the interconnect **W3** when a voltage is applied to the
25 interconnect **W2**, by the applied voltage. The capacitance **C32** is a value obtained by dividing a charge induced in the interconnect **W2** when a voltage is applied to the interconnect **W3**, by the applied voltage.

In the capacitance measuring circuit, there are placed three PMISFETs 1, 2 and 3 (charge-side switching transistors) placed in parallel with one another and three NMISFETs 4, 5 and 6 (discharge-side switching transistors) connected in series to the PMISFETs 1, 2 and 3, respectively. The sources of the PMISFETs 1, 2 and 3 are commonly connected via a charging voltage supply part to a power supply pad PST for supplying a power supply voltage V_{dd} , while the sources of the NMISFETs 4, 5 and 6 are commonly connected via a discharging part to a ground pad GND (voltage V_{ss}). The drains of the PMISFET 1 and the NMISFET 4 are connected via a node N1 to the interconnect W1. The drains of the PMISFET 2 and the NMISFET 5 are connected via a node N2 to the interconnect W2. The drains of the PMISFET 3 and the NMISFET 6 are connected via a node N3 to the interconnect W3.

That is, the interconnect W1 is connected via the PMISFET 1 to the charging voltage supply part and the power supply pad PST, the interconnect W2 is connected via the PMISFET 2 to the charging voltage supply part and the power supply pad PST, and the interconnect W3 is connected via the PMISFET 3 to the charging voltage supply part and the power supply pad PST.

Although not shown in Figure 1, the power supply pad PST is also connected to an active region (substrate region) of each of the PMISFETs 1, 2 and 3, and the ground pad GND is also connected to an active region of each of the NMISFETs 4, 5, 6, 7, 8, and 9, whereby these pads supply potentials to the substrates.

The interconnect W1 is connected via the node N1 and the NMISFET 7 (third switching transistor for measuring current) through a current sampling part to a current-monitoring pad 41. The interconnect W2 is connected via the node N2 and the NMISFET 8 (first or second switching transistor for measuring current) through the current sampling part to the current-monitoring pad 41. The interconnect W3 is connected via the node N3 and the NMISFET 9 (second or first switching transistor for measuring current) through the current sampling part to the current-monitoring pad 41. That is, all

of the interconnects **W1**, **W2** and **W3** are connected to the current-monitoring pad **41** through the common current-sampling part and are configured so that their currents **I** can be measured by bringing a probe of an ammeter **45** into contact with the current-monitoring pad **41**. The outlet side of the ammeter **45** is fixed at the ground level
 5 (0V).

A control circuit **31**, an oscillator **32** for generating a clock signal having a higher frequency than an external clock signal and a frequency divider **33** are connected in parallel to one another between the power supply pad **PST** (voltage **Vdd**) and the ground pad **GND** (voltage **Vss**). The control circuit **31** operates in synchronization with a
 10 high-frequency clock signal **Clk** generated by the oscillator **32** and applies a bias for ON/OFF switching to each of the gates **G1** through **G9** of the MISFETs **1** through **9**. A high-frequency signal output from the oscillator **32** is input to an input part of the frequency divider **33**, and an output part of the frequency divider **33** is connected to a frequency-monitoring pad **43**.

15 According to the semiconductor device of this embodiment, in the capacitance measuring circuit, the interconnect **W1** that is the first conductor member is connected via the PMISFET **1** that is the charge-side switching transistor to the charging voltage supply part, the interconnect **W2** (or **W3**) that is the second conductor member and the interconnect **W3** (or **W2**) that is the third conductor member are connected to the
 20 current-sampling part via the NMISFETs **8** and **9** that are the switching transistors for measuring current, respectively, and the interconnect **W2** (or **W3**) that is the second conductor member is connected to the charging voltage supply part via the PMISFET **2** (or **3**) that is the charge-side switching transistor. Therefore, it becomes possible to measure the capacitance **C23** between the interconnects **W2** and **W3** (or the capacitance **C32**
 25 between the interconnects **W3** and **W2**) in addition to the capacitance **C12** between the interconnects **W1** and **W2** and the capacitance **C13** between the interconnects **W1** and **W3**.

Furthermore, the interconnects **W2** and **W3** are connected to the charging voltage supply part via the PMISFET **2** and **3** that are the charge-side switching transistors, and the interconnect **W1** is connected to the current-sampling part via the NMISFET **7** that is the switching transistor for measuring current. Therefore, as will be described later, it becomes possible to separately measure all the capacitive components among the three interconnects **W1**, **W2** and **W3**, i.e., the capacitances **C12** and **C21** between the interconnects **W1** and **W2**, the capacitances **C13** and **C31** between the interconnects **W1** and **W3** and the capacitances **C23** and **C32** between the interconnects **W2** and **W3**.

Moreover, the interconnects **W1**, **W2** and **W3** are connected via the NMISFETs **4**, **5** and **6** that are the discharge switching transistors, respectively, through the discharge part to the ground pad. Therefore, in a mode for measuring the capacitance between two interconnects, it becomes possible to fix the potential of an interconnect that is not involved in the capacitance measurement, thereby preventing the accuracy of measuring the capacitance from being deteriorated due to the influence of the interconnect that is not involved in the capacitance measurement.

The capacitance measuring circuit of this embodiment has the advantages that the inclusion of the oscillator **32** therein allows the control circuit **31** to generate a waveform by applying a clock signal having a higher frequency than an external clock signal to the control circuit **31** and the inclusion of the frequency divider **33** therein simplifies the external monitoring of the frequency.

Figure 2 is a timing diagram illustrating the time variation of gate biases **Vg1** through **Vg9** that are output from the control circuit **31** in the capacitance measurement using the capacitance measuring circuit and are applied to the gates **G1** through **G9** of the MISFETs **1** through **9**. In this figure, T_{12} denotes the period during which the capacitance **C12** is monitored, T_{13} denotes the period during which the capacitance **C13** is monitored, T_{21} denotes the period during which the capacitance **C21** is monitored, T_{23} denotes the period during which the capacitance **C23** is monitored, T_{31} denotes the period during

which the capacitance **C31** is monitored, and **T₃₂** denotes the period during which the capacitance **C32** is monitored. Although not shown in Figure 2, the power supply voltage **Vdd** is fixed at a voltage **Vcc**, and the ground voltage **Vss** is fixed at 0V.

-Control during the period **T₁₂**-

5 First, the NMISFETs **4, 5** and **6** are ON at a timing **t10**, because the gate biases **Vg4**, **Vg5** and **Vg6** of the NMISFETs **4, 5** and **6** are all at H level. The PMISFETs **1, 2** and **3** are OFF, because the gate biases **Vg1**, **Vg2** and **Vg3** of the NMISFETs **1, 2** and **3** are all at H level. The NMISFETs **7, 8** and **9** are OFF, because the gate biases **Vg7**, **Vg8** and **Vg9** of the NMISFETs **7, 8** and **9** are all at L level. Since at this time the NMISFETs **4, 5** and **6** are ON and the PMISFET **1, 2** and **3** are OFF, charges on the nodes **N1**, **N2** and **N3** are all released into the ground.

At a timing **t11**, the gate biases **Vg4** and **Vg5** of the NMISFETs **4** and **5** change to L level so that the NMISFETs **4** and **5** turn OFF. Therefore, the nodes **N1** and **N2** are cut off from the ground pad **GND**.

15 Next, at a timing **t12**, the gate bias **Vg8** of the NMISFET **8** changes to H level so that the NMISFET **8** turns ON. Therefore, the interconnect **W2** is brought into conduction with the current-monitoring pad **41** via the node **N2**.

Next, at a timing **t13**, the gate bias **Vg1** of the PMISFET **1** changes to L level so that the PMISFET **1** turns ON. Therefore, the interconnect **W1** is brought into conduction with the power supply pad **PST** via the node **N1**, and thus the interconnect **W1** is charged.

20 Accordingly, when the probe of the ammeter **45** is brought into contact with the current-monitoring pad **41** during a period from the timing **t13** to the timing **t14** to measure the current **I**, the capacitance value **C12** between the interconnects **W1** and **W2** can be measured from the current **I** corresponding to the charge induced in the interconnect **W2** when the voltage **Vcc** is applied to the interconnect **W1**, on the basis of the following formula (5):

$$C12=I/(Vcc \cdot f) \quad (5)$$

where $f(=1/T)$ is the frequency of the gate input waveform and T denotes the time from the timing **t10** to the timing **t17**.

Thereafter, gate biases are changed such that the operations opposite to those at the timings **t13**, **t12**, **t11**, and **t10** are carried out at the timings **t14**, **t15**, **t16**, and **t17**,
 5 respectively. Finally, the control state at the timing **17** is returned to the same state as at the timing **t10**.

During the period T_{12} , the PMISFET **1** and the NMISFET **4** or the NMISFET **7** are not ON simultaneously. Thus, a flow-through current that flows through the PMISFET **1** and the NMISFET **4** or the NMISFET **7** does not flow from the power supply pad **PST**
 10 into the current-monitoring pad **41** and the ground pad **GND**. During the period T_{12} , the PMISFETs **2** and **3** are always OFF. Thus, the interconnects **W2** and **W3** are not charged with the voltage V_{cc} . Moreover, during the period T_{12} , the NMISFETs **7** and **9** are always OFF. Thus, the nodes **N1** and **N3** are not brought into conduction with the current-monitoring pad **41**, and consequently currents from the interconnects **W1** and **W3**
 15 are not observed. Since during the period T_{12} the gate bias V_{g6} of the NMISFET **6** is always at H level, the NMISFET **6** is always ON, and the potential of the node **N3** is fixed at 0V. Therefore, the capacitance relating to the interconnect **W3** is not observed.

-Control during the period T_{13} -

First, at a timing **t20**, each of the gate biases V_{g1} through V_{g9} of the MISFETs **1**
 20 through **9** is at the same voltage level as at the timing **t10** during the period T_{12} .

At a timing **t21**, the gate biases V_{g4} and V_{g6} of the NMISFETs **4** and **6** change to L level so that the NMISFETs **4** and **6** turn OFF. Therefore, the nodes **N1** and **N3** are cut off from the ground pad **GND**.

Next, at a timing **t22**, the gate bias V_{g9} of the NMISFET **9** changes to H level so
 25 that the NMISFET **9** turns ON. Therefore, the interconnect **W3** is brought into conduction with the current-monitoring pad **41** via the node **N3**.

Next, at a timing **t23**, the gate bias V_{g1} of the PMISFET **1** changes to L level so that

the PMISFET 1 turns ON. Therefore, the interconnect W1 is brought into conduction with the power supply pad PST via the node N1, and thus the interconnect W1 is charged.

Accordingly, when the probe of the ammeter 45 is brought into contact with the current-monitoring pad 41 during a period from the timing t23 to the timing t24 to measure the current I, the capacitance value C13 between the interconnects W1 and W3 can be measured from the current I corresponding to the charge induced in the interconnect W3 when the voltage Vcc is applied to the interconnect W1, on the basis of the following formula (6):

$$C13=I/(V_{cc} \cdot f) \quad (6)$$

where $f(=1/T)$ is the frequency of the gate input waveform and T denotes the time from the timing t20 to the timing t27.

Thereafter, gate biases are changed such that the operations opposite to those at the timings t23, t22, t21, and t20 are carried out at the timings t24, t25, t26, and t27, respectively. Finally, the control state at the timing 27 is returned to the same state as at the timing t20.

During the period T₁₃, the PMISFET 1 and the NMISFET 4 or the NMISFET 7 are not ON simultaneously. Thus, a flow-through current that flows through the PMISFET 1 and the NMISFET 4 or the NMISFET 7 does not flow from the power supply pad PST into the current-monitoring pad 41 and the ground pad GND. During the period T₁₃, the PMISFETs 2 and 3 are always OFF. Thus, the interconnects W2 and W3 are not charged with the voltage Vcc. Moreover, during the period T₁₃, the NMISFETs 7 and 8 are always OFF. Thus, the nodes N1 and N2 are not brought into conduction with the current-monitoring pad 41, and consequently currents from the interconnects W1 and W2 are not observed. Since during the period T₁₃ the gate bias Vg5 of the NMISFET 5 is always at H level, the NMISFET 5 is always ON, and the potential of the node N2 is fixed at 0V. Therefore, the capacitance relating to the interconnect W2 is not observed.

-Control during the period T₂₁-

First, at a timing **t30**, each of the gate biases **Vg1** through **Vg9** of the MISFETs **1** through **9** is at the same voltage level as at the timing **t10** during the period **T₁₂**.

At a timing **t31**, the gate biases **Vg4** and **Vg5** of the NMISFETs **4** and **5** change to L level so that the NMISFETs **4** and **5** turn OFF. Therefore, the nodes **N1** and **N2** are cut off from the ground pad **GND**.

Next, at a timing **t32**, the gate bias **Vg7** of the NMISFET **7** changes to H level so that the NMISFET **7** turns ON. Therefore, the interconnect **W1** is brought into conduction with the current-monitoring pad **41** via the node **N1**.

Next, at a timing **t33**, the gate bias **Vg2** of the PMISFET **2** changes to L level so that the PMISFET **2** turns ON. Therefore, the interconnect **W2** is brought into conduction with the power supply pad **PST** via the node **N2**, and thus the interconnect **W2** is charged.

Accordingly, when the probe of the ammeter **45** is brought into contact with the current-monitoring pad **41** during a period from the timing **t33** to the timing **t34** to measure the current **I**, the capacitance value **C21** between the interconnects **W2** and **W1** can be measured from the current **I** corresponding to the charge induced in the interconnect **W1** when the voltage **Vcc** is applied to the interconnect **W2**, on the basis of the following formula (7):

$$C21=I/(V_{cc} \cdot f) \quad (7)$$

where $f(=1/T)$ is the frequency of the gate input waveform and **T** denotes a time from the timing **t30** to the timing **t37**.

Thereafter, gate biases are changed such that the operations opposite to those at the timings **t33**, **t32**, **t31**, and **t30** are carried out at the timings **t34**, **t35**, **t36**, and **t37**, respectively. Finally, the control state at the timing **t37** is returned to the same state as at the timing **t30**.

During the period **T₂₁**, the PMISFET **2** and the NMISFET **5** or the NMISFET **8** are not ON simultaneously. Thus, a flow-through current that flows through the PMISFET **2** and the NMISFET **5** or the NMISFET **8** does not flow from the power supply pad **PST**

into the current-monitoring pad 41 and the ground pad GND. During the period T_{21} , the PMISFETs 1 and 3 are always OFF. Thus, the interconnects W1 and W3 are not charged with the voltage V_{cc} . Moreover, during the period T_{21} , the NMISFETs 7 and 9 are always OFF. Thus, the nodes N1 and N3 are not brought into conduction with the current-monitoring pad 41, and consequently currents from the interconnects W1 and W3 are not observed. Since during the period T_{21} the gate bias V_{g6} of the NMISFET 6 is always at H level, the NMISFET 6 is always ON, and the potential of the node N3 is fixed at 0V. Therefore, the capacitance relating to the interconnect W3 is not observed.

-Control during the period T_{23} -

First, at a timing t_{40} , each of the gate biases V_{g1} through V_{g9} of the MISFETs 1 through 9 is at the same voltage level as at the timing t_{10} during the period T_{12} .

At a timing t_{41} , the gate biases V_{g5} and V_{g6} of the NMISFETs 5 and 6 change to L level so that the NMISFETs 5 and 6 turn OFF. Therefore, the nodes N1 and N3 are cut off from the ground pad GND.

Next, at a timing t_{42} , the gate bias V_{g9} of the NMISFET 9 changes to H level so that the NMISFET 9 turns ON. Therefore, the interconnect W3 is brought into conduction with the current-monitoring pad 41 via the node N3.

Next, at a timing t_{43} , the gate bias V_{g2} of the PMISFET 2 changes to L level so that the PMISFET 2 turns ON. Therefore, the interconnect W2 is brought into conduction with the power supply pad PST via the node N2, and thus the interconnect W2 is charged.

Accordingly, when the probe of the ammeter 45 is brought into contact with the current-monitoring pad 41 during a period from the timing t_{43} to the timing t_{44} to measure the current I , the capacitance value C_{23} between the interconnects W2 and W3 can be measured from the current I corresponding to the charge induced in the interconnect W3 when the voltage V_{cc} is applied to the interconnect W2, on the basis of the following formula (8):

$$C_{23} = I / (V_{cc} \cdot f) \quad (8)$$

where $f(=1/T)$ is the frequency of the gate input waveform and T denotes the time from the timing **t40** to the timing **t47**.

Thereafter, gate biases are changed such that the operations opposite to those at the timings **t43**, **t42**, **t41**, and **t40** are carried out at the timings **t44**, **t45**, **t46**, and **t47**, respectively. Finally, the control state at the timing **t47** is returned to the same state as at the timing **t40**.

During the period T_{23} , the PMISFET **2** and the NMISFET **5** or the NMISFET **8** are not ON simultaneously. Thus, a flow-through current that flows through the PMISFET **2** and the NMISFET **5** or the NMISFET **8** does not flow from the power supply pad **PST** into the current-monitoring pad **41** and the ground pad **GND**. During the period T_{23} , the PMISFETs **1** and **3** are always OFF. Thus, the interconnects **W1** and **W3** are not charged with the voltage V_{cc} . Moreover, during the period T_{23} , the NMISFETs **7** and **8** are always OFF. Thus, the nodes **N1** and **N2** are not brought into conduction with the current-monitoring pad **41**, and consequently currents from the interconnects **W1** and **W2** are not observed. Since during the period T_{23} the gate bias V_{g4} of the NMISFET **4** is always at H level, the NMISFET **4** is always ON, and the potential of the node **N1** is fixed at 0V. Therefore, the capacitance relating to the interconnect **W1** is not observed.

-Control during the period T_{31} -

First, at a timing **t50**, each of the gate biases V_{g1} through V_{g9} of the MISFETs **1** through **9** is at the same voltage level as at the timing **t10** during the period T_{12} .

At a timing **t51**, the gate biases V_{g4} and V_{g6} of the NMISFETs **4** and **6** change to L level so that the NMISFETs **4** and **6** turn OFF. Therefore, the nodes **N1** and **N3** are cut off from the ground pad **GND**.

Next, at a timing **t52**, the gate bias V_{g7} of the NMISFET **7** changes to H level so that the NMISFET **7** turns ON. Therefore, the interconnect **W1** is brought into conduction with the current-monitoring pad **41** via the node **N1**.

Next, at a timing **t53**, the gate bias V_{g3} of the PMISFET **3** changes to L level so that

the PMISFET 3 turns ON. Therefore, the interconnect W3 is brought into conduction with the power supply pad PST via the node N3, and thus the interconnect W3 is charged.

Accordingly, when the probe of the ammeter 45 is brought into contact with the current-monitoring pad 41 during a period from the timing t53 to the timing t54 to measure the current I, the capacitance value C31 between the interconnects W3 and W1 can be measured from the current I corresponding to the charge induced in the interconnect W1 when the voltage Vcc is applied to the interconnect W3, on the basis of the following formula (9):

$$C31=I/(V_{cc} \cdot f) \quad (9)$$

where $f(=1/T)$ is the frequency of the gate input waveform and T denotes the time from the timing t50 to the timing t57.

Thereafter, gate biases are changed such that the operations opposite to those at the timings t53, t52, t51, and t50 are carried out at the timings t54, t55, t56, and t57, respectively. Finally, the control state at the timing t57 is returned to the same state as at the timing t50.

During the period T₃₁, the PMISFET 3 and the NMISFET 6 or the NMISFET 9 are not ON simultaneously. Thus, a flow-through current that flows through the PMISFET 3 and the NMISFET 6 or the NMISFET 9 does not flow from the power supply pad PST into the current-monitoring pad 41 and the ground pad GND. During the period T₃₁, the PMISFETs 1 and 2 are always OFF. Thus, the interconnects W1 and W2 are not charged with the voltage Vcc. Moreover, during the period T₃₁, the NMISFETs 8 and 9 are always OFF. Thus, the nodes N2 and N3 are not brought into conduction with the current-monitoring pad 41, and consequently currents from the interconnects W2 and W3 are not observed. Since during the period T₃₁ the gate bias Vg5 of the NMISFET 5 is always at H level, the NMISFET 5 is always ON, and the potential of the node N2 is fixed at 0V. Therefore, the capacitance relating to the interconnect W2 is not observed.

-Control during the period T₃₂-

First, at a timing **t60**, each of the gate biases **Vg1** through **Vg9** of the MISFETs **1** through **9** is at the same voltage level as at the timing **t10** during the period T_{12} .

At a timing **t61**, the gate biases **Vg5** and **Vg6** of the NMISFETs **5** and **6** change to L level so that the NMISFETs **5** and **6** turn OFF. Therefore, the nodes **N2** and **N3** are cut off from the ground pad **GND**.

Next, at a timing **t62**, the gate bias **Vg8** of the NMISFET **8** changes to H level so that the NMISFET **8** turns ON. Therefore, the interconnect **W2** is brought into conduction with the current-monitoring pad **41** via the node **N2**.

Next, at a timing **t63**, the gate bias **Vg3** of the PMISFET **3** changes to L level so that the PMISFET **3** turns ON. Therefore, the interconnect **W3** is brought into conduction with the power supply pad **PST** via the node **N3**, and thus the interconnect **W3** is charged.

Accordingly, when the probe of the ammeter **45** is brought into contact with the current-monitoring pad **41** during a period from the timing **t63** to the timing **t64** to measure the current **I**, the capacitance value **C32** between the interconnects **W3** and **W2** can be measured from the current **I** corresponding to the charge induced in the interconnect **W1** when the voltage **Vcc** is applied to the interconnect **W3**, on the basis of the following formula (10):

$$C32 = I / (V_{cc} \cdot f) \quad (10)$$

where $f(=1/T)$ is the frequency of the gate input waveform and **T** denotes the time from the timing **t60** to the timing **t67**.

Thereafter, gate biases are changed such that the operations opposite to those at the timings **t63**, **t62**, **t61**, and **t60** are carried out at the timings **t64**, **t65**, **t66**, and **t67**, respectively. Finally, the control state at the timing **t67** is returned to the same state as at the timing **t60**.

During the period T_{32} , the PMISFET **3** and the NMISFET **6** or the NMISFET **9** are not ON simultaneously. Thus, a flow-through current that flows through the PMISFET **3** and the NMISFET **6** or the NMISFET **9** does not flow from the power supply pad **PST**

into the current-monitoring pad 41 and the ground pad GND. During the period T_{32} , the PMISFETs 1 and 2 are always OFF. Thus, the interconnects W1 and W2 are not charged with the voltage V_{cc} . Moreover, during the period T_{32} , the NMISFETs 7 and 9 are always OFF. Thus, the nodes N1 and N3 are not brought into conduction with the
 5 current-monitoring pad 41, and consequently currents from the interconnects W1 and W3 are not observed. Since during the period T_{32} the gate bias V_{g4} of the NMISFET 4 is always at H level, the NMISFET 4 is always ON, and the potential of the node N1 is fixed at 0V. Therefore, the capacitance relating to the interconnect W1 is not observed.

According to the capacitance measuring circuit of this embodiment, when there exist
 10 three interconnects W1, W2 and W3, the capacitances C21, C23, C31, and C32 can be measured by charging the interconnects W2 and W3, besides the capacitances C12 and C13 that can be observed by charging the interconnect W1.

In addition, only five pads are necessary for this embodiment. Therefore, the number of pads can be significantly decreased as compared with the number of pads, seven,
 15 that is required for the known capacitance measuring circuit shown in Figure 7, resulting in the reduced area of the semiconductor device.

(Embodiment 2)

Figure 3 is a circuit diagram illustrating the structure of a capacitance measuring circuit placed in a semiconductor device (LSI) according to a second embodiment. The
 20 capacitance measuring circuit located in the semiconductor device of this embodiment is configured to measure the capacitance (parasitic capacitance) between each two of three conductor members forming a target capacitor section.

As shown in Figure 3, the target capacitor section in the semiconductor device of this embodiment is also provided with three conductor members each two opposed with
 25 dielectrics interposed therebetween. However, unlike the first embodiment, the three conductor members of this embodiment are a source/drain region SD (first conductor member) formed by doping part of a semiconductor substrate with impurities, a substrate

region **SUB** (second conductor member) corresponding to a well and a gate electrode **GT** (third conductor member).

On the other hand, the structure of the capacitance measuring circuit is the same as that of the first embodiment. Capacitances between the source/drain region **SD** and the substrate region **SUB** are designated **Cdb** (corresponding to **C12**) and **Cbd** (corresponding to **C21**), capacitances between the source/drain region **SD** and the gate electrode **GT** are designated **Cdg** (corresponding to **C13**) and **Cgd** (corresponding to **C31**), and capacitances between the substrate region **SUB** and the gate electrode **GT** are designated **Cbg** (corresponding to **C23**) and **Cgb** (corresponding to **C32**). In this relation, the capacitance **Cdb** is a value obtained by dividing a charge induced in the substrate region **SUB** when a voltage is applied to the source/drain region **SD**, by the applied voltage. The capacitance **Cbd** is a value obtained by dividing a charge induced in the source/drain region **SD** when a voltage is applied to the substrate region **SUB**, by the applied voltage. The capacitance **Cdg** is a value obtained by dividing a charge induced in the gate electrode **GT** when a voltage is applied to the source/drain region **SD**, by the applied voltage. The capacitance **Cgd** is a value obtained by dividing a charge induced in the source/drain region **SD** when a voltage is applied to the gate electrode **GT**, by the applied voltage. The capacitance **Cbg** is a value obtained by dividing a charge induced in the gate electrode **GT** when a voltage is applied to the substrate region **SUB**, by the applied voltage. The capacitance **Cgb** is a value obtained by dividing a charge induced in the substrate region **SUB** when a voltage is applied to the gate electrode **GT**, by the applied voltage.

Figure 4 is a cross sectional view of the semiconductor device of this embodiment. As shown in this figure, the semiconductor device of this embodiment has a structure in which the target capacitor section is surrounded by a triple well.

This figure shows the cross sectional structure of the target capacitor section and the capacitance measuring circuit that are part of a logic circuit located in the semiconductor device but does not show the other regions such as a memory region and a peripheral

circuit region.

The semiconductor substrate is partitioned into plural active regions by isolation regions **55** having a shallow trench structure. In the semiconductor substrate, there are provided a P-well **51** occupying most of the semiconductor substrate, a deep N-well **52** the lower side of which is surrounded by the P-well **51**, a P-well **53** the lower side of which is covered by the deep N-well **52**, and an N-well **54** for separating the P-wells **53** and **51** from each other.

The NMISFET of the target capacitor section comprises a source/drain region **56** (SD) formed by doping the P-well **53** corresponding to the substrate region SUB with N-type impurities, and a gate electrode **61** (GT). On the other hand, the NMISFET of the capacitance measuring circuit comprises a source/drain region **58** formed by doping the P-well **51** with N-type impurities, and a gate electrode **62**.

Also in this embodiment, when the capacitances **C12** and **C21** in the first embodiment are replaced with the capacitances **Cdb** and **Cbd**, the capacitances **C13** and **C31** are replaced with the capacitances **Cdg** and **Cgd**, and the capacitances **C23** and **C32** are replaced with the capacitances **Cbg** and **Cgb**, each of the capacitances **Cdb**, **Cbd**, **Cdg**, **Cgd**, **Cbg**, and **Cgb** can be measured utilizing the control method shown in Figure 2 and the formulae (5) through (10).

Since this embodiment employs, particularly, the structure of the semiconductor device in which the target capacitor section is surrounded by the triple well, capacitances between each two of members of the MISFET can be measured with high accuracy, while noises from the MISFET in the capacitance measuring circuit operating by a high-frequency clock are cut off.

Furthermore, when the voltages of the power supply pad **PST**, the ground pad **GND** and the pad **41** for measuring current are changed, the capacitances can be measured in an arbitrary voltage state. In particular, the MIS capacitance has a voltage dependency. The voltage dependencies of the capacitances can be measured by the following formula

(11).

$$C(v)=\{I(V+\delta V)-I(V)\}/f \quad (11)$$

(Embodiment 3)

Figure 5 is a circuit diagram illustrating the structure of a capacitance measuring circuit placed in a semiconductor device (LSI) according to a third embodiment. The capacitance measuring circuit located in the semiconductor device of this embodiment is configured to measure the capacitance (parasitic capacitance) between each two of three conductor members forming a target capacitor section.

Also in this embodiment, as shown in Figure 5, an interconnect **W1** (first conductor member), an interconnect **W2** (second conductor member) and an interconnect **W3** (third conductor member) are placed as three conductor members in the target capacitor section. The target capacitor section is configured to measure the capacitances **C12** and **C21** between the interconnects **W1** and **W2**, the capacitances **C13** and **C31** between the interconnects **W1** and **W3**, and the capacitances **C23** and **C32** between the interconnects **W2** and **W3**.

The structure of the capacitance measuring circuit of this embodiment is characterized in that two MISFETs **7a** and **7b** that are equivalent to the NMISFET **7** in the first embodiment are connected in series, two MISFETs **8a** and **8b** that are equivalent to the NMISFET **8** are connected in series, and two MISFETs **9a** and **9b** that are equivalent to the NMISFET **9** are connected in series. The pairs of MISFETs receive common gate biases **Vg7**, **Vg8** and **Vg9**, respectively. While one of each pair of MISFETs (for example, NMISFET **7a**, **8a** or **9a**) is a current-monitoring MISFET having the same threshold voltage as the NMISFETs **7**, **8** or **9** in the first embodiment, the other (for example, NMISFETs **7b**, **8b** or **9b**) is a MISFET for suppressing off-leakage current, which has a higher threshold voltage than the NMISFETs **7**, **8** and **9** in the first embodiment. The other structure is identical with the structure of the measuring circuit shown in Figure 1.

Also in the capacitance measuring circuit of this embodiment, the capacitances **C12** and **C21** between the interconnects **W1** and **W2**, the capacitances **C13** and **C31** between the interconnects **W1** and **W3**, and the capacitances **C23** and **C32** between the interconnects **W2** and **W3** can be measured utilizing the control method shown in Figure 2
 5 and the formulae (5) through (10).

According to the capacitance measuring circuit of this embodiment, as in the first embodiment, the capacitances **C12**, **C21**, **C13**, **C31**, **C23**, and **C32** between each two of the three conductor members can be measured while the number of pads is decreased.

In addition, since in the capacitance measuring circuit of this embodiment, a
 10 current-monitoring MISFET (for example, NMISFETs **7a**, **8a** or **9a**) and a MISFET for suppressing off-leakage current (for example, NMISFET **7b**, **8b** or **9b**) having a higher threshold voltage than the current-monitoring MISFET are placed in series between each of the nodes **N1**, **N2** and **N3** and the pad **41** for measuring current, this effectively decreases leakage current.

15 Furthermore, since the operations of the current-monitoring MISFET and the MISFET for suppressing off-leakage current are controlled by a common control signal (a gate bias **Vg7**, **Vg8** or **Vg9**), a redundant control circuit is unnecessary. Therefore, the structure of the control circuit can be simplified.

When the capacity to drive the current-monitoring MISFET is less necessary, the
 20 number of MISFETs placed in series with that current-monitoring MISFET can be increased, thereby enhancing the effect of decreasing leakage current.

The conductor members in the third embodiment are not limited to the interconnects **W1**, **W2** and **W3** but may be a source/drain region, a substrate region and a gate electrode as shown in Figures 3 and 4.

25 (Embodiment 4)

Figure 6 is a circuit diagram illustrating the structure of a capacitance measuring circuit for measuring the capacitances of capacitors placed in a semiconductor device (LSI)

according to a fourth embodiment. The capacitance measuring circuit located in the semiconductor device of this embodiment is configured to measure the capacitance between each two of three conductor members forming a target capacitor section.

Also in this embodiment, as shown in Figure 6, an interconnect **W1** (first conductor member), an interconnect **W2** (second conductor member) and an interconnect **W3** (third conductor member) are placed as three conductor members in the target capacitor section. The target capacitor section is configured to measure the capacitances **C12** and **C21** between the interconnects **W1** and **W2**, the capacitances **C13** and **C31** between the interconnects **W1** and **W3**, and the capacitances **C23** and **C32** between the interconnects **W2** and **W3**.

The structure of the capacitance measuring circuit of this embodiment is characterized in that there are provided power supply pads **PST1** and **PST2** for individually supplying power supply voltages **Vdd1** (for example, 0.1V) and **Vdd2** (for example, 1.2V) to the capacitance measuring circuit and the interconnects **W1**, **W2** and **W3** of the target capacitor section. The configurations of the other parts are identical with those of the first embodiment.

Also in the capacitance measuring circuit of this embodiment, the capacitances **C12** and **C21** between the interconnects **W1** and **W2**, the capacitances **C13** and **C31** between the interconnects **W1** and **W3**, and the capacitances **C23** and **C32** between the interconnects **W2** and **W3** can be measured utilizing the control method shown in Figure 2 and the formulae (5) through (10).

According to the capacitance measuring circuit of this embodiment, as in the first embodiment, the capacitances **C12**, **C21**, **C13**, **C31**, **C23**, and **C32** between each two of the three conductor members can be measured while the number of pads is decreased.

In addition, since in the semiconductor device of this embodiment there are provided power supply pads **PST1** and **PST2** for individually supplying power supply voltages **Vdd1** and **Vdd2** to the capacitance measuring circuit and the interconnects **W1**, **W2** and

W3 of the target capacitor section, the following effects can be delivered.

The power supply voltage V_{dd1} supplied to the interconnects W1, W2 and W3 is not for controlling the operations of the MISFETs. Thus, the voltage V_{dd1} is not required to be much high. The reason is that the gate biases V_{g1} through V_{g9} of the MISFETs 1 through 9 are supplied from the control circuit 31. If the voltage between the source and drain in each of the MISFETs 1 through 9 is lowered, the operating speed of that MISFET 1 through 9 may be decreased to some extent. In such a case, since the operating frequency is lowered, the function of measuring the capacitances is not degraded. When the voltages applied to the interconnects W1, W2 and W3 are increased, noises are easily included in the currents I to be measured. Contrarily, when, as in this embodiment, the power supply voltage V_{dd1} is decreased, the occurrence of the noise can be suppressed.

On the other hand, the power supply voltage V_{dd2} supplied to a capacitance sampling part such as the control circuit 31 is for controlling the operations of the MISFETs. Thus, in order to keep the operating speeds of the MISFETs high, the voltage V_{dd2} must be high to some extent. Even when the power supply voltage V_{dd2} is made higher, the occurrence of noise has less effect on the operation of each MISFET. In general, noises of the substrate lead to inconveniences for an analog circuit but present no problem for a logic circuit.

The conductor members of the fourth embodiment are not limited to the interconnects W1, W2 and W3 but may be a source/drain region, a substrate region and a gate electrode as shown in Figures 3 and 4. In the capacitance measuring circuit of the fourth embodiment, each of the NMISFETs 7, 8 and 9 may comprise plural MISFETs placed in series as shown in Figure 5.

The number of conductor members placed in the target capacitor section, for example, interconnects, may be four or more. Also in this case, if, as shown in Figures 1, 3, 5, and 6, one PMISFET and two NMISFETs are placed for each of the conductor

members, then the capacitance between each two of the interconnects can be measured.

In each of the embodiments, the semiconductor substrate includes a substrate wholly made of a semiconductor (for example, a semiconductor such as Si, Ge or GaAs), an SOI substrate, and a substrate having a heterojunction (for example, a Si/SiGe-type semiconductor substrate).

According to the semiconductor device of the present invention, the capacitances (parasitic capacitances) among three or more conductor members can be measured separately while the number of necessary pads is decreased.